

**Triple phase leg
Fast Trench + Field Stop IGBT®
Power Module**

**$V_{CES} = 1200V$
 $I_C = 75A @ T_c = 80^\circ C$**

Application

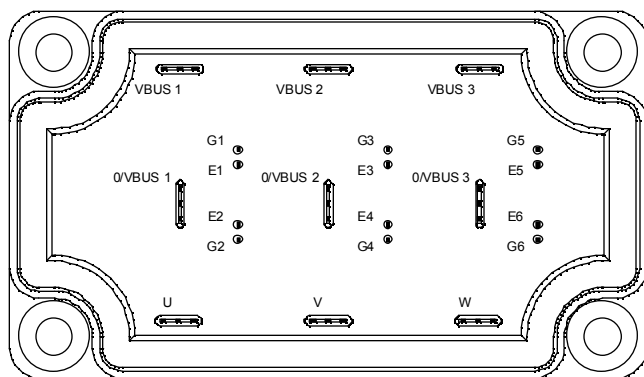
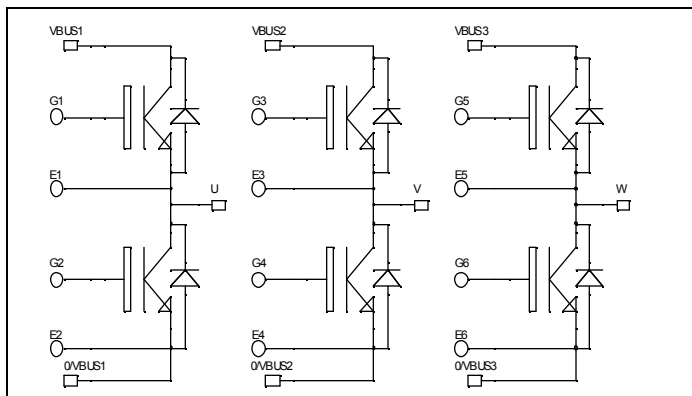
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$ 100 $T_C = 80^\circ C$ 75	A
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$ 175	
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$ 350	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$ 150A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$, $V_{CE} = 1200\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 75\text{A}$	$T_j = 25^\circ\text{C}$ 1.4	$T_j = 125^\circ\text{C}$ 1.7	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3\text{mA}$	5.0		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

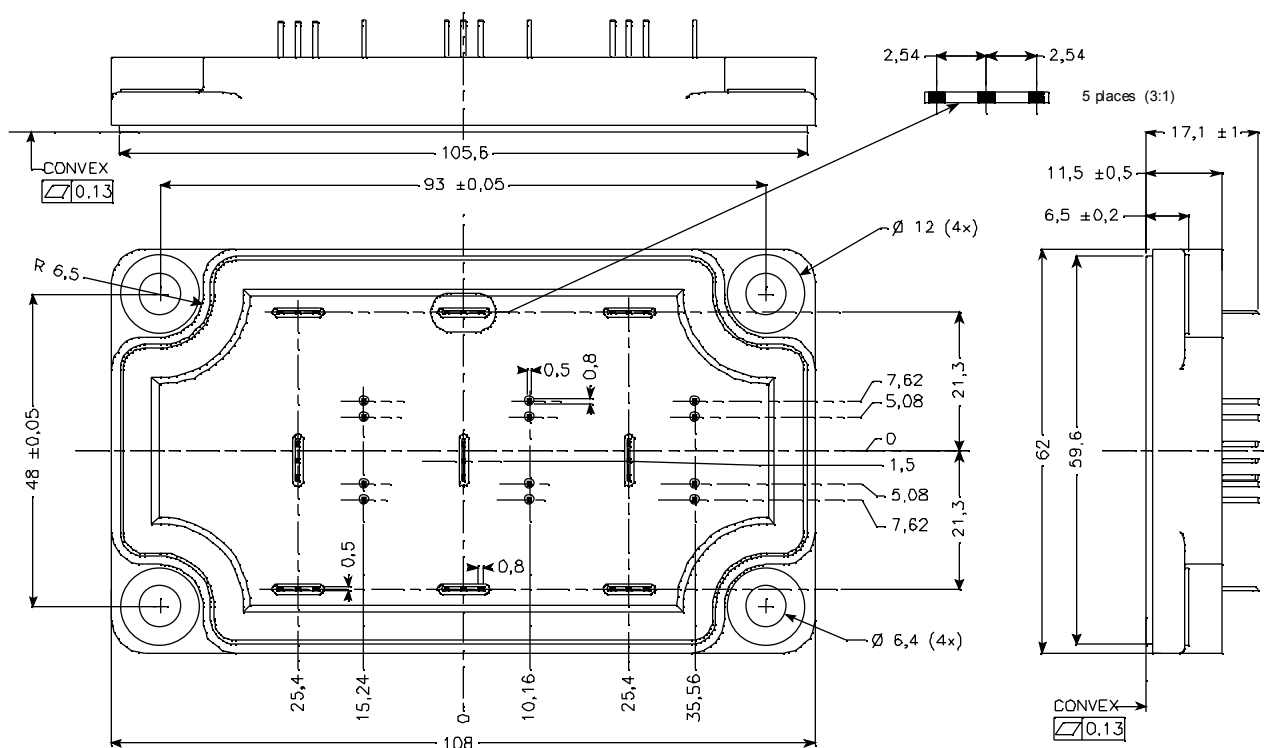
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		5340		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		280		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		240		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		260		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$		30		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75\text{A}$		420		
T_f	Fall Time	$R_G = 4.7\Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		285		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$		50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75\text{A}$		520		
T_f	Fall Time	$R_G = 4.7\Omega$		90		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $T_j = 125^\circ\text{C}$		7		mJ
E_{off}	Turn-off Switching Energy	$I_C = 75\text{A}$ $R_G = 4.7\Omega$ $T_j = 125^\circ\text{C}$		8.1		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		250 500	μA
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		75		A
V_F	Diode Forward Voltage	$I_F = 75\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1	V
t_{rr}	Reverse Recovery Time	$I_F = 75\text{A}$ $V_R = 600\text{V}$ $di/dt = 2000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	170 280		ns
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	7 14		μC
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	3 5.5		mJ

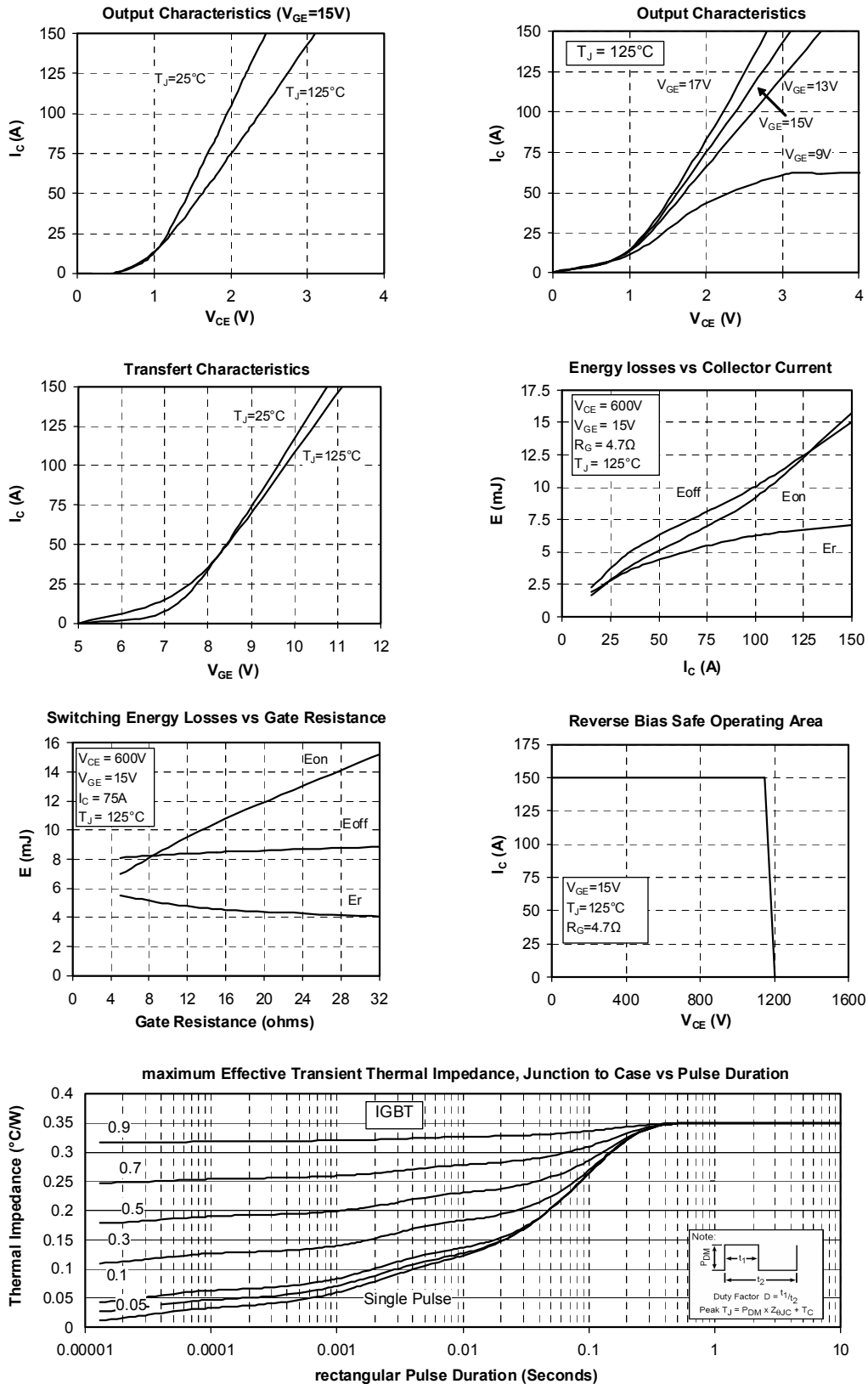
Thermal and package characteristics
Symbol Characteristic

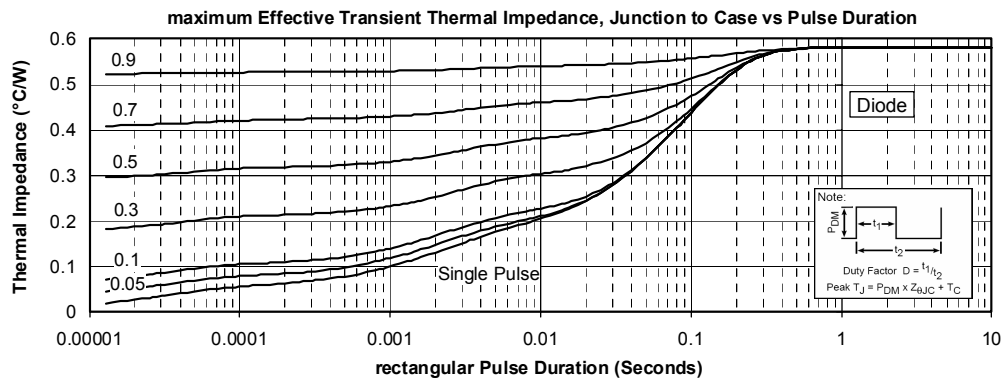
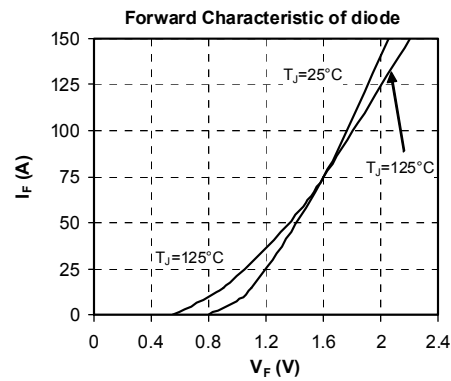
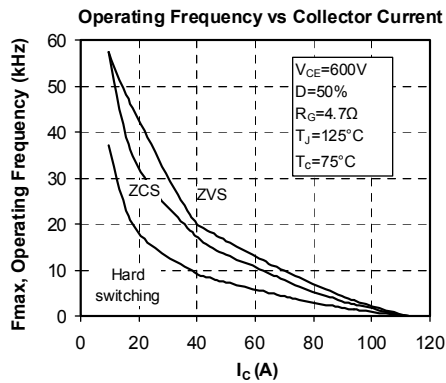
			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.35	°C/W
		Diode			0.58	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1$ mA, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

SP6-P Package outline (dimensions in mm)


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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